

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27154	Application No. 10/708,430		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Michael P. Belyansky et al.			
				Filing Date March 3, 2004		Group 2818	
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EXAMINER /Andy Huynh/ (05/26/2006)				DATE CONSIDERED			
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